



**74V2G03**

## DUAL 2-INPUT OPEN DRAIN NAND GATE

- HIGH SPEED:  $t_{PD} = 3.9\text{ns}$  (TYP.) at  $V_{CC} = 5\text{V}$
- LOW POWER DISSIPATION:  
 $I_{CC} = 1\mu\text{A}$ (MAX.) at  $T_A = 25^\circ\text{C}$
- HIGH NOISE IMMUNITY:  
 $V_{NIH} = V_{NIL} = 28\% V_{CC}$  (MIN.)
- POWER DOWN PROTECTION ON INPUTS
- OPERATING VOLTAGE RANGE:  
 $V_{CC(OPR)} = 2\text{V}$  to  $5.5\text{V}$
- IMPROVED LATCH-UP IMMUNITY

### DESCRIPTION

The 74V2G03 is an advanced high-speed CMOS DUAL 2-INPUT OPEN DRAIN NAND GATE fabricated with sub-micron silicon gate and double-layer metal wiring C<sup>2</sup>MOS technology. The internal circuit is composed of 3 stages including buffer output, which provide high noise immunity and stable output. The device can, with an external pull-up resistor, be used in wired AND configuration. This device



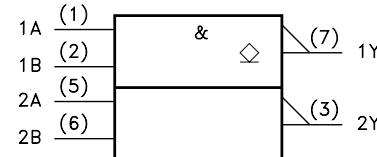
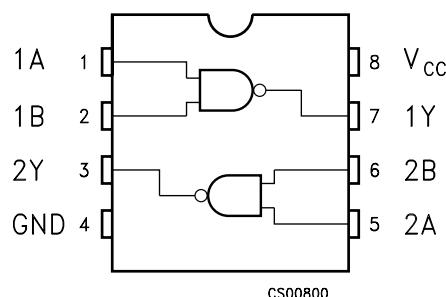
SOT23-8L

### ORDER CODES

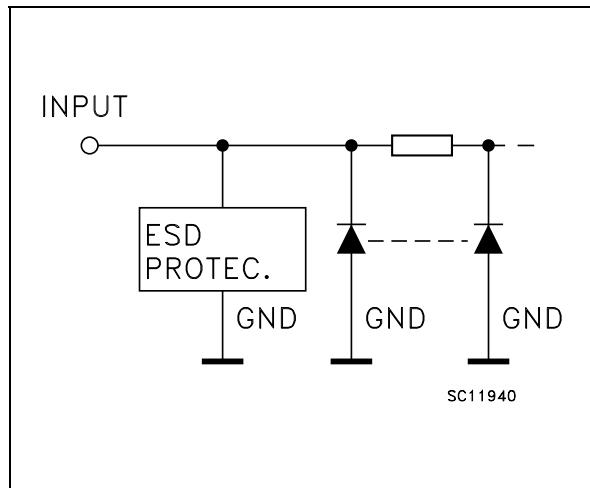
PACKAGE	T & R
SOT23-8L	74V2G03STR

can also be used as a led driver in any other application requiring current sink. Power down protection is provided on all inputs and 0 to 7V can be accepted on inputs with no regard to the supply voltage. This device can be used to interface 5V to 3V.

### PIN CONNECTION AND IEC LOGIC SYMBOLS



**INPUT EQUIVALENT CIRCUIT**



**PIN DESCRIPTION**

PIN N°	SYMBOL	NAME QND FUNCTION
1, 5	1A, 2A	Data Input
2, 6	1B, 2B	Data Input
7, 3	1Y, 2Y	Data Output
4	GND	Ground (0V)
8	V <sub>CC</sub>	Positive Supply Voltage

**TRUTH TABLE**

A	B	Y
L	L	Z
L	H	Z
H	L	Z
H	H	L

Z: High Impedance

**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	-0.5 to +7.0	V
V <sub>I</sub>	DC Input Voltage	-0.5 to +7.0	V
V <sub>O</sub>	DC Output Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	- 20	mA
I <sub>OK</sub>	DC Output Diode Current	± 20	mA
I <sub>O</sub>	DC Output Current	± 25	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current	± 50	mA
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
T <sub>L</sub>	Lead Temperature (10 sec)	260	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

**RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	2 to 5.5	V
V <sub>I</sub>	Input Voltage	0 to 5.5	V
V <sub>O</sub>	Output Voltage	0 to V <sub>CC</sub>	V
T <sub>op</sub>	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time (note 1) (V <sub>CC</sub> = 3.3 ± 0.3V) (V <sub>CC</sub> = 5.0 ± 0.5V)	0 to 100 0 to 20	ns/V ns/V

1) V<sub>IN</sub> from 30% to 70% of V<sub>CC</sub>

## DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value						Unit	
		V <sub>CC</sub> (V)		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V <sub>IH</sub>	High Level Input Voltage	2.0		1.5			1.5		1.5		V
		3.0 to 5.5		0.7V <sub>CC</sub>			0.7V <sub>CC</sub>		0.7V <sub>CC</sub>		
V <sub>IL</sub>	Low Level Input Voltage	2.0				0.5		0.5		0.5	V
		3.0 to 5.5				0.3V <sub>CC</sub>		0.3V <sub>CC</sub>		0.3V <sub>CC</sub>	
V <sub>OL</sub>	Low Level Output Voltage	2.0	I <sub>O</sub> =50 μA		0.0	0.1		0.1		0.1	V
		3.0	I <sub>O</sub> =50 μA		0.0	0.1		0.1		0.1	
		4.5	I <sub>O</sub> =50 μA		0.0	0.1		0.1		0.1	
		3.0	I <sub>O</sub> =4 mA			0.36		0.44		0.55	
		4.5	I <sub>O</sub> =8 mA			0.36		0.44		0.55	
I <sub>OZ</sub>	High Impedance Output Leakage Current	5.5	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> V <sub>O</sub> = V <sub>CC</sub> or GND			± 0.25		± 2.5		± 5	μA
I <sub>I</sub>	Input Leakage Current	0 to 5.5	V <sub>I</sub> = 5.5V or GND			± 0.1		± 1		± 1	μA
I <sub>CC</sub>	Quiescent Supply Current	5.5	V <sub>I</sub> = V <sub>CC</sub> or GND			1		10		20	μA

## AC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Condition			Value						Unit	
		V <sub>CC</sub> (V)	C <sub>L</sub> (pF)		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t <sub>PZL</sub>	Propagation Delay Time	3.3 <sup>(*)</sup>	15			4.8	6.5	1.0	8.0	1.0	9.0	ns
		3.3 <sup>(*)</sup>	50			5.3	7.5	1.0	9.0	1.0	10.0	
		5.0 <sup>(**)</sup>	15			3.9	5.5	1.0	6.5	1.0	7.5	
		5.0 <sup>(**)</sup>	50			4.3	6.0	1.0	7.5	1.0	8.5	
t <sub>PLZ</sub>	Propagation Delay Time	3.3 <sup>(*)</sup>	50			6.8	9.5	1.0	10.0	1.0	11.0	ns
		5.0 <sup>(**)</sup>	50			4.8	6.5	1.0	7.0	1.0	8.0	

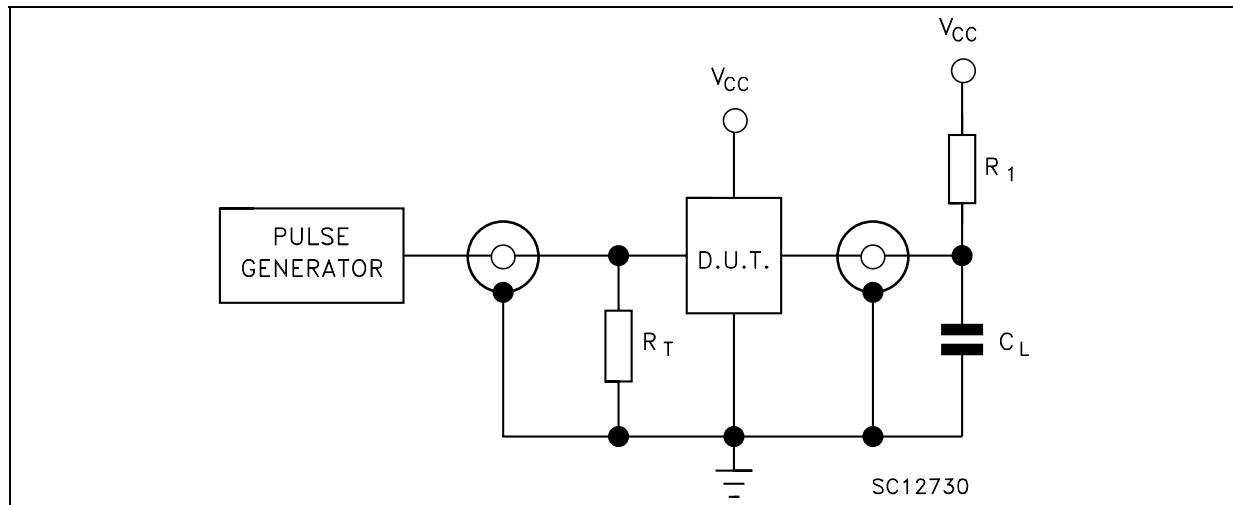
<sup>(\*)</sup> Voltage range is 3.3V ± 0.3V<sup>(\*\*)</sup> Voltage range is 5.0V ± 0.5V

## CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition		Value						Unit
		$T_A = 25^\circ\text{C}$			-40 to $85^\circ\text{C}$		-55 to $125^\circ\text{C}$			
		Min.	Typ.	Max.	Min.	Max.	Min.	Max.		
$C_{IN}$	Input Capacitance			4	10		10		10	pF
$C_{OUT}$	Output Capacitance			5	10		10		10	pF
$C_{PD}$	Power Dissipation Capacitance (note 1)			3						pF

1)  $C_{PD}$  is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation.  $I_{CC(\text{opr})} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/2$

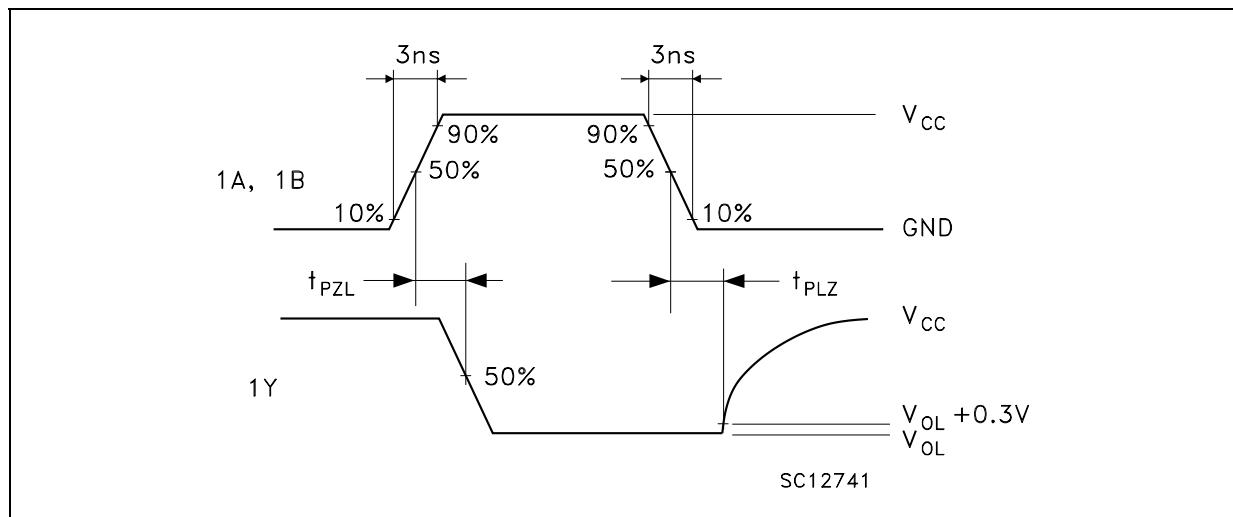
## TEST CIRCUIT



$C_L = 15/50\text{pF}$  or equivalent (includes jig and probe capacitance)

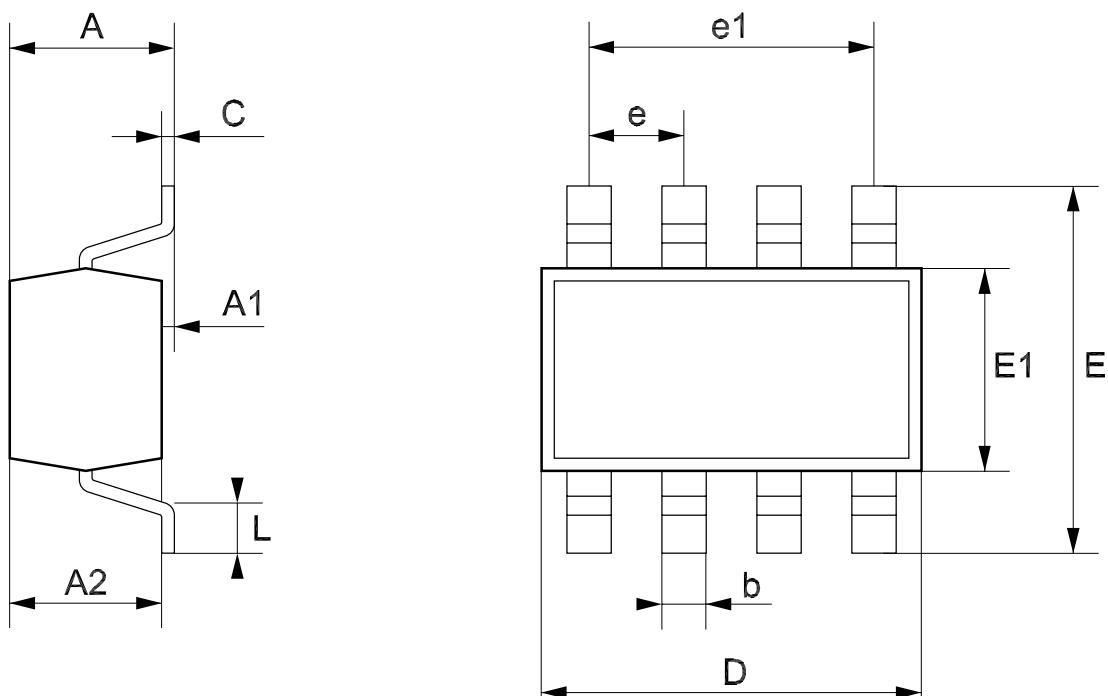
$R_1 = 1\text{K}\Omega$  or equivalent

$R_T = Z_{OUT}$  of pulse generator (typically  $50\Omega$ )

WAVEFORM: PROPAGATION DELAY ( $f=1\text{MHz}$ ; 50% duty cycle)

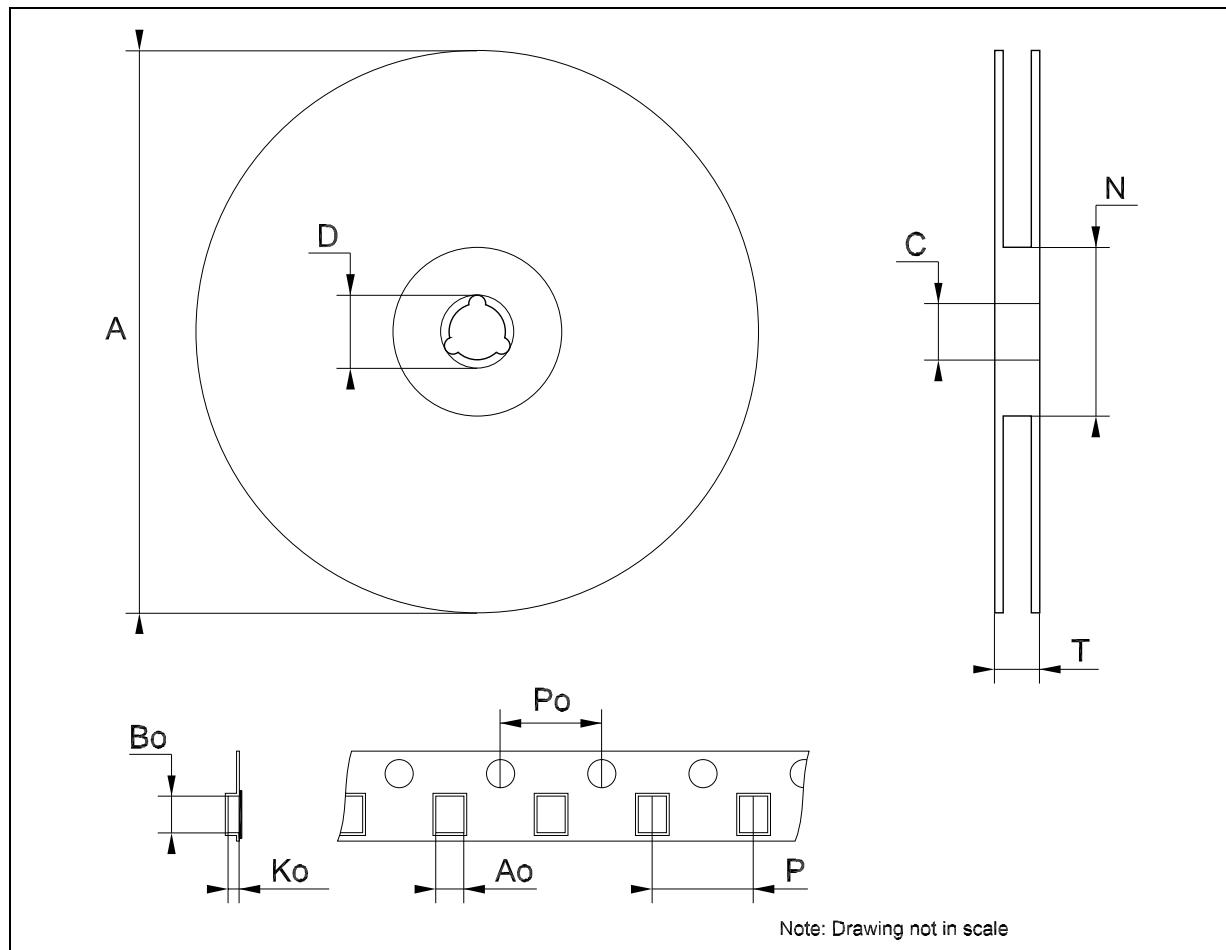
SOT23-8L MECHANICAL DATA						
DIM.	mm.			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	0.90		1.45	35.4		57.1
A1	0.00		0.15	0.0		5.9
A2	0.90		1.30	35.4		51.2
b	0.22		0.38	8.6		14.9
C	0.09		0.20	3.5		7.8
D	2.80		3.00	110.2		118.1
E	2.60		3.00	102.3		118.1
E1	1.50		1.75	59.0		68.8
e	0	.65			25.6	
e1		1.95			76.7	
L	0.35		0.55	13.7		21.6

DIM.	mm.			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	0.90		1.45	35.4		57.1
A1	0.00		0.15	0.0		5.9
A2	0.90		1.30	35.4		51.2
b	0.22		0.38	8.6		14.9
C	0.09		0.20	3.5		7.8
D	2.80		3.00	110.2		118.1
E	2.60		3.00	102.3		118.1
E1	1.50		1.75	59.0		68.8
e	0	.65			25.6	
e1		1.95			76.7	
L	0.35		0.55	13.7		21.6



**Tape & Reel SOT23-xL MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			180			7.086
C	12.8	13.0	13.2	0.504	0.512	0.519
D	20.2			0.795		
N	60			2.362		
T			14.4			0.567
Ao	3.13	3.23	3.33	0.123	0.127	0.131
Bo	3.07	3.17	3.27	0.120	0.124	0.128
Ko	1.27	1.37	1.47	0.050	0.054	0.058
Po	3.9	4.0	4.1	0.153	0.157	0.161
P	3.9	4.0	4.1	0.153	0.157	0.161



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